gost.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
Hiroki et al.	
Serial No.:	"Express Mail" Mailing Label No. EL 828231479
	Date of Deposit July 13, 2001
Filed: Herewith	I hereby certify that this correspondence is being
For: Semiconductor Display Device And Method	deposited with the United States Postal Service Express Mail Post Office to Addressee" service
Of Driving A Semiconductor Display Device	under 37 CF.3 1.10 on the date indicated above
Examiner:	and is addressed to: Commissioner for Patents, Washington, D.C. 20231
	Name <u>Ruben M. Gamez</u> (typed or printed)
Art Unit:	
	Signature Kulen M. Lang
Commissioner for Patents	
Washington D.C. 20231	

PRELIMINARY AMENDMENT A

Prior to examination, please enter the following amendment in the above-identified application:

IN THE CLAIMS:

Please amend the claims as follows:

16 (Amended) A semiconductor display device according to claim 1, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

17 (Amended). A computer using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

18 (Amended). A video camera using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

19 (Amended). A DVD player using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

Please add the following new claims:

25 (New). A semiconductor display device according to claim 2, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

26 (New). A semiconductor display device according to claim 3, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

27 (New). A semiconductor display device according to claim 4, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

28 (New). A semiconductor display device according to claim 5, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

29 (New). A semiconductor display device according to claim 6, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

30 (New). A semiconductor display device according to claim 7, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

- 31 (New). A semiconductor display device according to claim 8, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.
- 32 (New). A semiconductor display device according to claim 9, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.
- 33 (New). A semiconductor display device according to claim 10, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.
- 34 (New). A semiconductor display device according to claim 11, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.
- 35 (New). A semiconductor display device according to claim 12, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.
- 36 (New). A semiconductor display device according to claim 13, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.
- 37 (New). A semiconductor display device according to claim 14, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.
- 38 (New). A semiconductor display device according to claim 15, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon. --

REMARKS

This amendment is being submitted to remove the improper dependency upon multi-dependent claims. It is believed that no new matter is being added. Accordingly, it is requested that this amendment be entered.

If any additional fee is due for this amendment, please charge our deposit account 50/1039.

Respectfully submitted,

Mark J. Murphy

Registration No. 34,225

COOK, ALEX, McFARRON, MANZO, CUMMINGS & MEHLER, Ltd. 200 West Adams Street, Suite 2850 Chicago, Illinois 60606 (312) 236-8500

Marked up copy of claims as amended:

16 (Amended) A semiconductor display device according to [any one of claims 1 to 15] <u>claim</u>
1, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

17 (Amended). A computer using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

18 (Amended). A video camera using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

19 (Amended). A DVD player using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

Please add the following new claims:

25 (New). A semiconductor display device according to claim 2, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

26 (New). A semiconductor display device according to claim 3, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

27 (New). A semiconductor display device according to claim 4, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

28 (New). A semiconductor display device according to claim 5, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

29 (New). A semiconductor display device according to claim 6, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

30 (New). A semiconductor display device according to claim 7, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

31 (New). A semiconductor display device according to claim 8, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

32 (New). A semiconductor display device according to claim 9, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

33 (New). A semiconductor display device according to claim 10, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

34 (New). A semiconductor display device according to claim 11, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

35 (New). A semiconductor display device according to claim 12, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

36 (New). A semiconductor display device according to claim 13, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

37 (New). A semiconductor display device according to claim 14, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

38 (New). A semiconductor display device according to claim 15, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon. --